



# STW55NM60ND

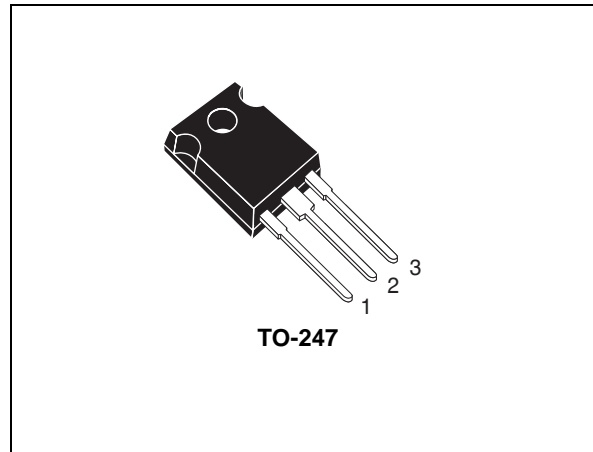
N-channel 600 V, 0.047  $\Omega$  typ., 51 A FDmesh™ II Power MOSFET (with fast diode) in a TO-247 package

Datasheet — production data

## Features

Type	V <sub>DSS</sub> (@T <sub>J</sub> max)	R <sub>DS(on)</sub> max	I <sub>D</sub>
STW55NM60ND	650 V	< 0.060 $\Omega$	51 A

- The worldwide best R<sub>DS(on)</sub> amongst the fast recovery diode devices in TO-247
- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance
- High dv/dt and avalanche capabilities



## Application

- Switching applications

## Description

This FDmesh™ II Power MOSFET with intrinsic fast-recovery body diode is produced using the second generation of MDmesh™ technology. Utilizing a new strip-layout vertical structure, this revolutionary device features extremely low on-resistance and superior switching performance. It is ideal for bridge topologies and ZVS phase-shift converters.

Figure 1. Internal schematic diagram

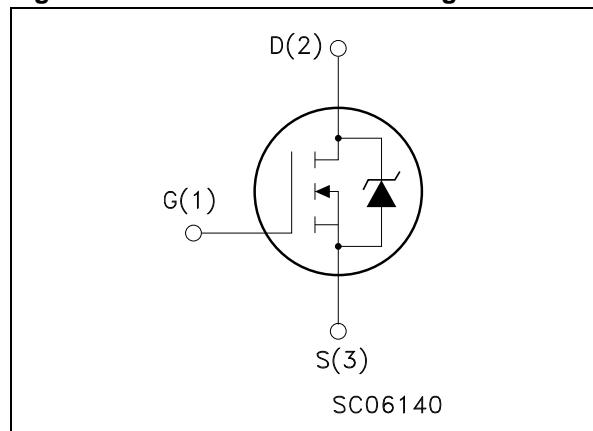


Table 1. Device summary

Order code	Marking	Package	Packaging
STW55NM60ND	55NM60ND	TO-247	Tube

# Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	600	V
$V_{GS}$	Gate- source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	51	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	32	A
$I_{DM}^{(1)}$	Drain current (pulsed)	204	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	350	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	40	V/ns
$T_{stg}$	Storage temperature	-55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

1. Pulse width limited by safe operating area

2.  $I_{SD} \leq 51\text{ A}$ ,  $di/dt \leq 600\text{ A}/\mu\text{s}$ ,  $V_{DD} = 80\% V_{(BR)DSS}$

**Table 3. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	0.36	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	50	$^\circ\text{C}/\text{W}$
$T_l$	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

**Table 4. Avalanche characteristics**

Symbol	Parameter	Max value	Unit
$I_{AS}$	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j$ max)	15	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$ , $I_D = I_{AS}$ , $V_{DD} = 50\text{ V}$ )	1600	mJ

## 2 Electrical characteristics

( $T_{CASE}=25^{\circ}C$  unless otherwise specified)

**Table 5. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}, V_{GS} = 0$	600			V
$dv/dt^{(1)}$	Drain source voltage slope	$V_{DD}=480 \text{ V}, I_D= 51 \text{ A}, V_{GS} = 10 \text{ V}$		30		V/ns
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 600 \text{ V}$ $V_{DS} = 600 \text{ V}, T_C = 125^{\circ}C$			10 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10 \text{ V}, I_D = 25.5 \text{ A}$		0.047	0.060	$\Omega$

1. Characteristic value at turn off on inductive load.

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15 \text{ V}, I_D = 25.5 \text{ A}$		45		S
$C_{iss}$ $C_{oss}$ $C_{rss}$	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 50 \text{ V}, f = 1 \text{ MHz}, V_{GS} = 0$		5800 300 30		pF pF pF
$C_{oss \text{ eq.}}^{(2)}$	Equivalent output capacitance	$V_{GS} = 0, V_{DS} = 0 \text{ to } 480 \text{ V}$		900		pF
$t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_f$	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD} = 300 \text{ V}, I_D = 25.5 \text{ A}$ $R_G = 4.7 \Omega, V_{GS} = 10 \text{ V}$ (see Figure 19), (see Figure 14)		33 68 188 96		ns ns ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 480 \text{ V}, I_D = 51 \text{ A}, V_{GS} = 10 \text{ V},$ (see Figure 15)		190 30 90		nC nC nC
$R_g$	Gate input resistance	f=1 MHz Gate DC Bias = 0 Test signal level = 20 mV Open drain		2.5		$\Omega$

1. Pulsed: pulse duration= 300  $\mu\text{s}$ , duty cycle 1.5%

2.  $C_{oss \text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current				51	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				204	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 51\text{ A}, V_{GS} = 0$			1.3	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 51\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s}$ <i>(see Figure 16)</i>		200		ns
$Q_{rr}$	Reverse recovery charge			1.8		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			18		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 51\text{ A}, V_{DD} = 60\text{ V}$ $di/dt = 100\text{ A}/\mu\text{s},$ $T_j = 150\text{ }^\circ\text{C}$ <i>(see Figure 16)</i>		280		ns
$Q_{rr}$	Reverse recovery charge			3.4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			24		A

1. Pulse width limited by safe operating area
2. Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

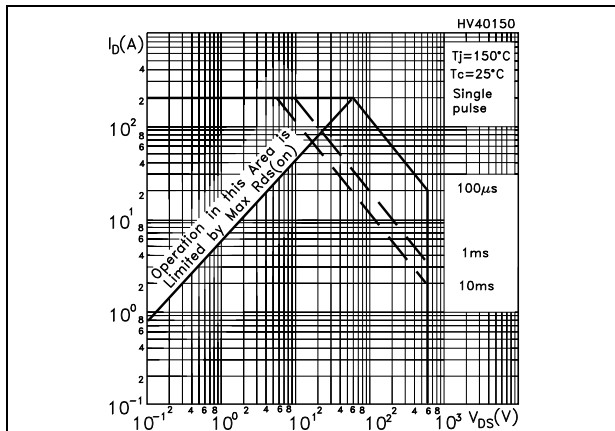


Figure 3. Thermal impedance

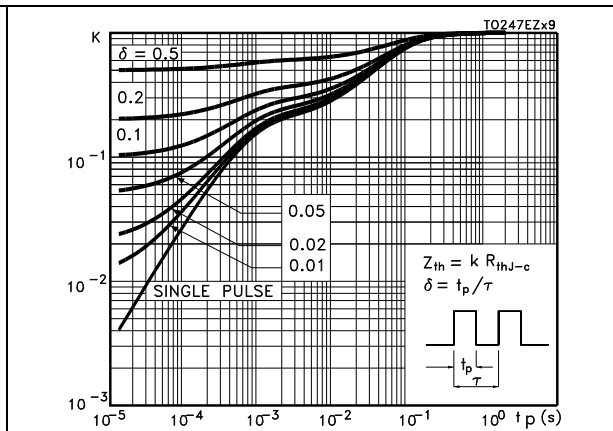


Figure 4. Output characteristics

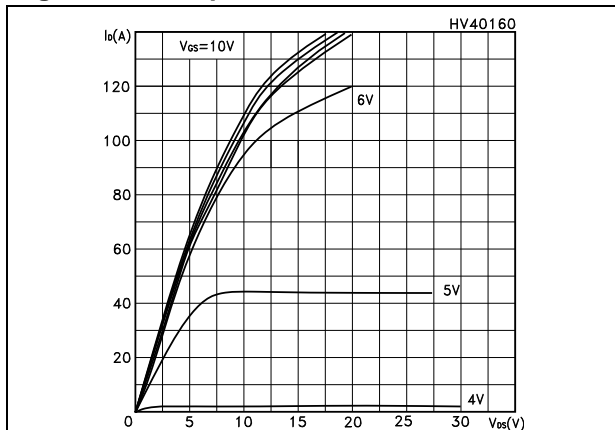


Figure 5. Transfer characteristics

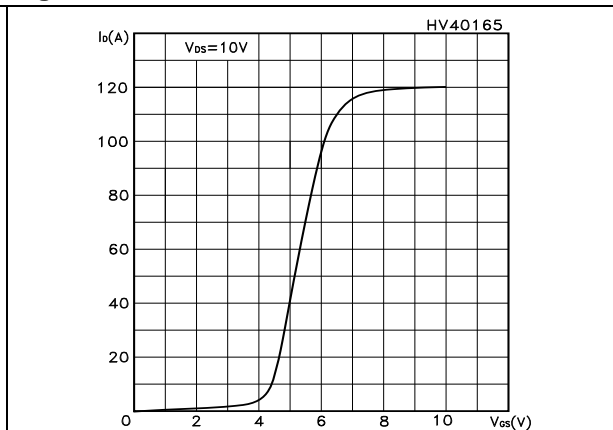


Figure 6. Transconductance

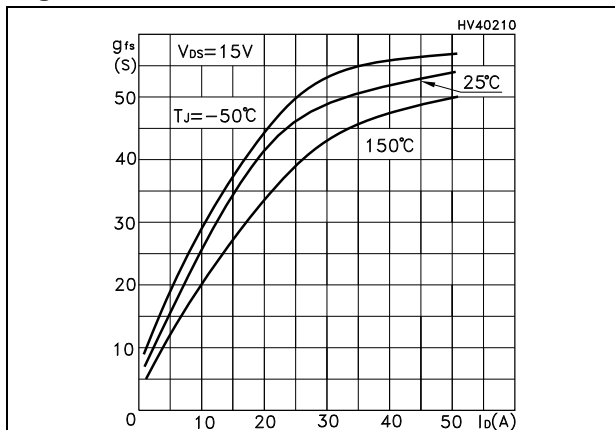


Figure 7. Static drain-source on-resistance

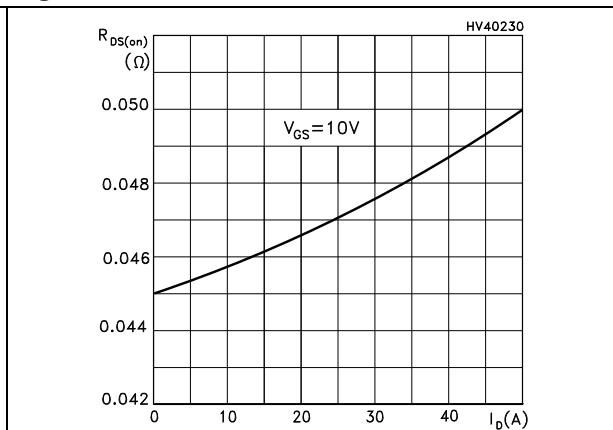


Figure 8. Gate charge vs gate-source voltage Figure 9. Capacitance variations

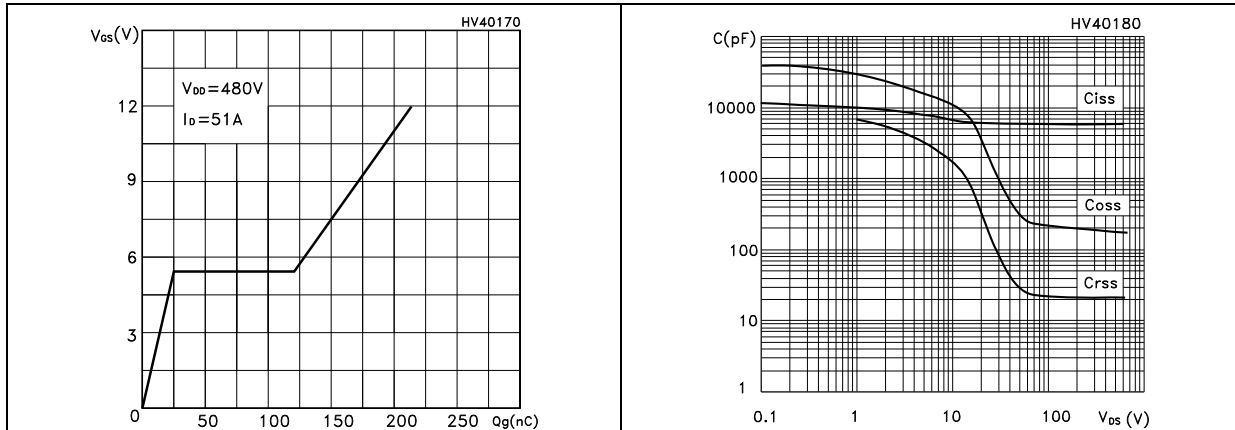


Figure 10. Normalized gate threshold voltage vs temperature Figure 11. Normalized on resistance vs temperature

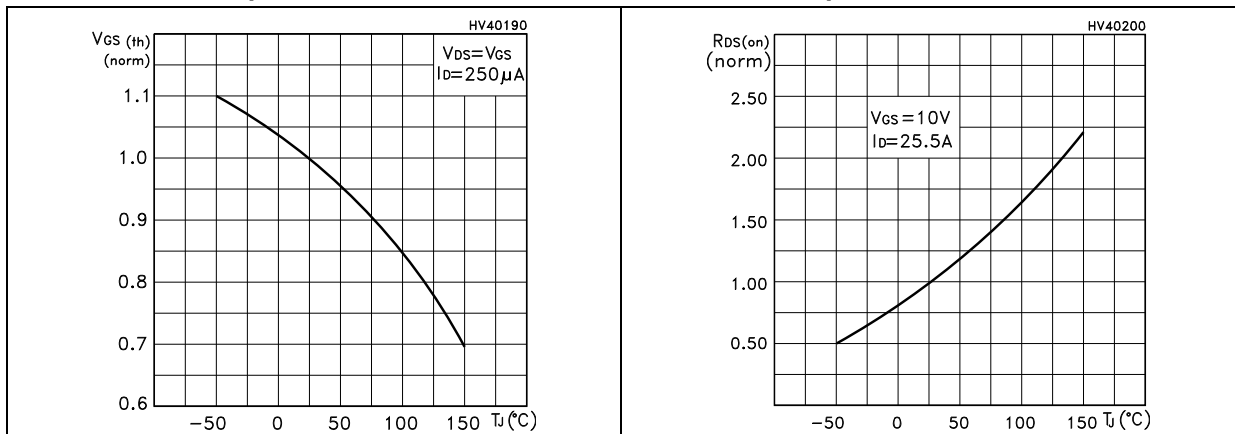
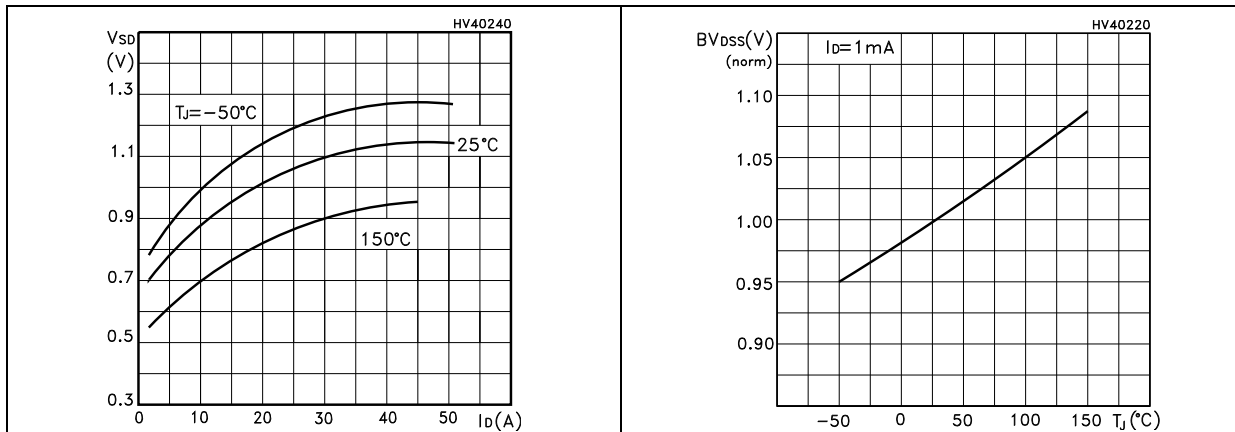
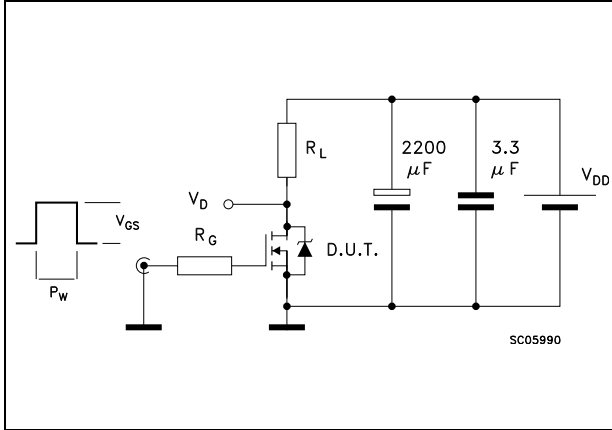


Figure 12. Source-drain diode forward characteristics Figure 13. Normalized  $B_{VDSS}$  vs temperature

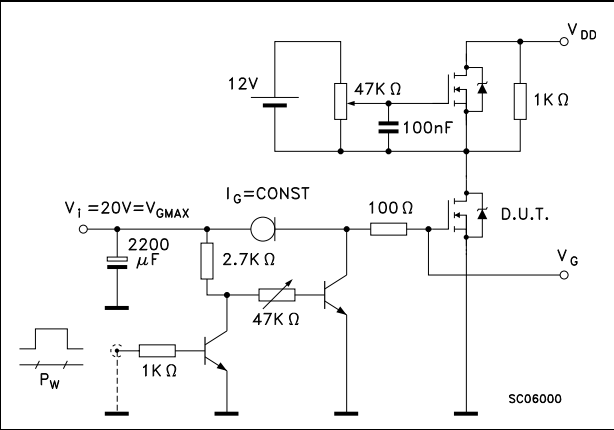


### 3 Test circuits

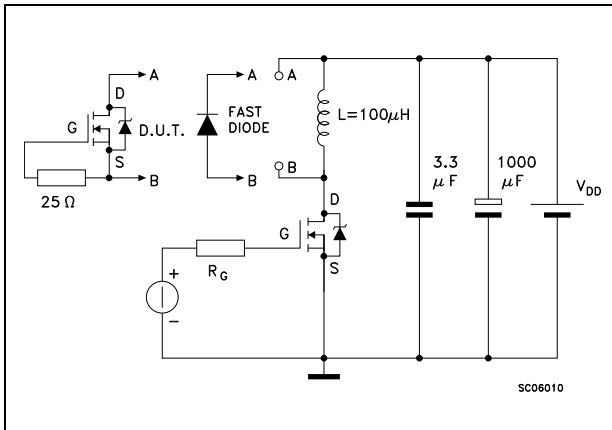
**Figure 14. Switching times test circuit for resistive load**



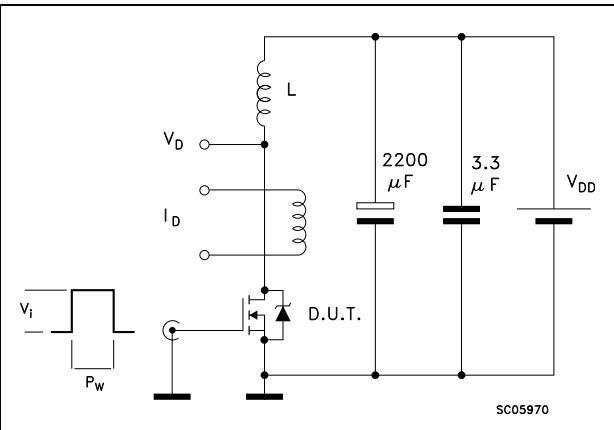
**Figure 15. Gate charge test circuit**



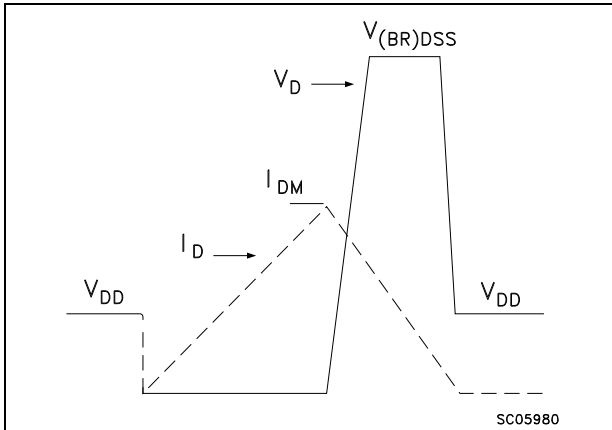
**Figure 16. Test circuit for inductive load switching and diode recovery times**



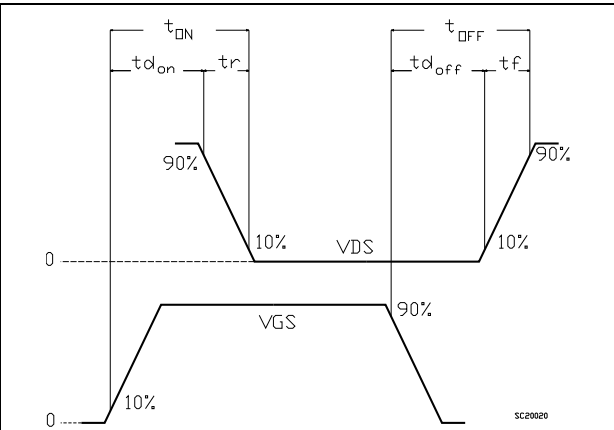
**Figure 17. Unclamped Inductive load test circuit**



**Figure 18. Unclamped inductive waveform**



**Figure 19. Switching time waveform**





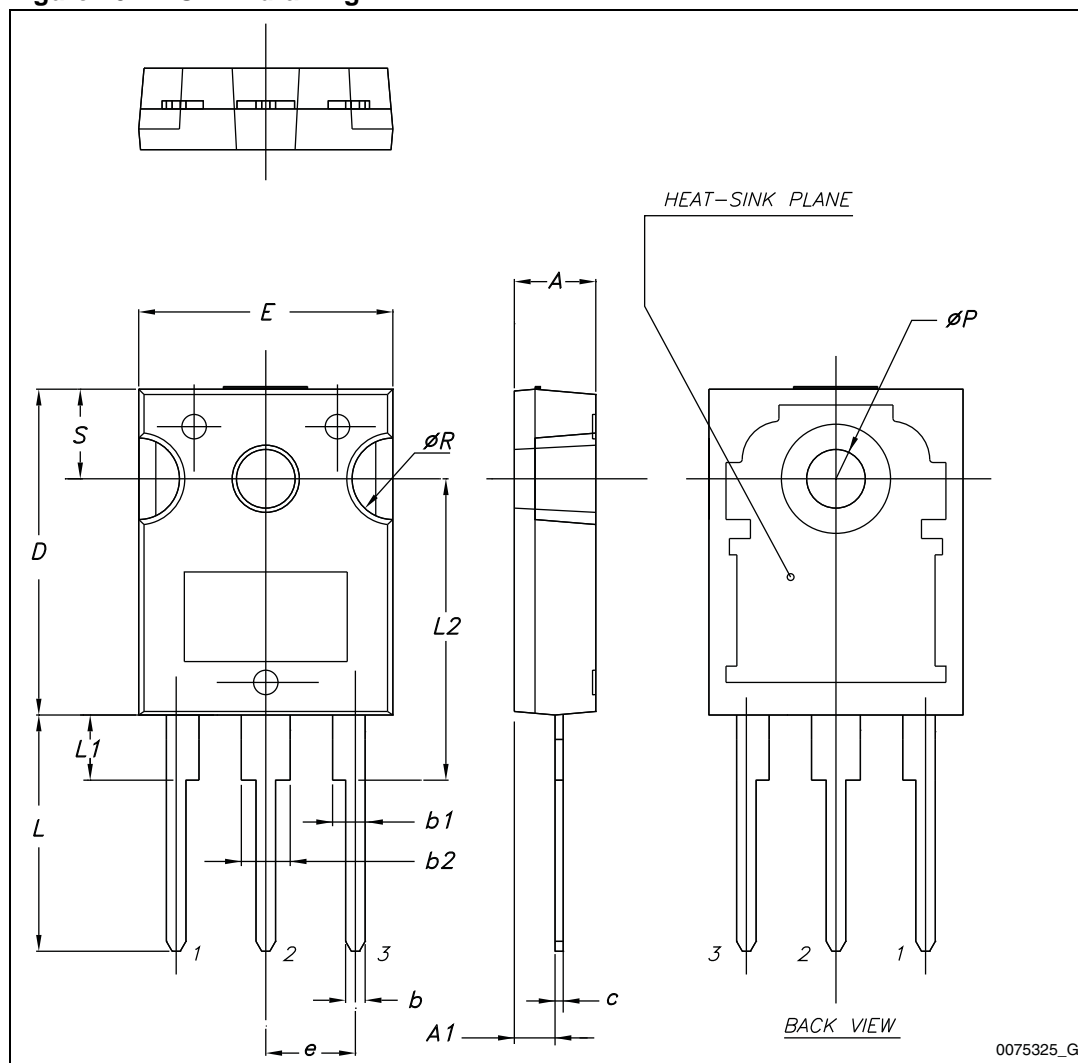
## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 8. TO-247 mechanical data**

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 20. TO-247 drawing



0075325\_G

## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
16-Nov-2007	1	First release.
22-Apr-2008	2	Document status promoted from preliminary data to datasheet.
19-Dec-2012	3	Title changed on the cover page. Minor text changes. Updated <a href="#">Section 4: Package mechanical data</a> .

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